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(71) Applicant: HITACHI LTD

(72) Inventor: HASHIMOTO KOJI KAWAMOTO YOSHIFUMI

KOBAYASHI TAKASHI

(74) Representative:

SILICON THIN FILM POLYCRYSTALLINE (54) FORMATION OF

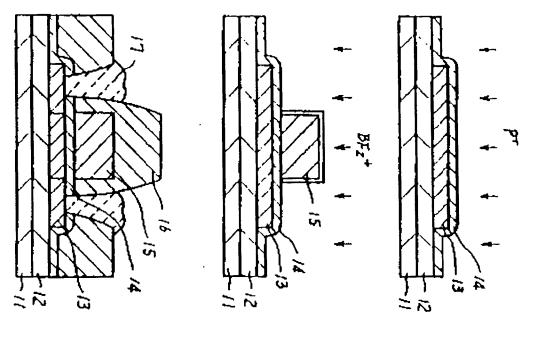
(57) Abstract:

a small absolute value of threshold characterized by a small OFF current, manufacture a polycrystalline Si an amorphous state at a specified reacting gas, performing deposition in by using disilane or trisilane as a voltage and a large operating current, MOS type field-effect transistor PURPOSE: To make it possible to temperature, performing a heat

treatment and polycrystallization.

a reacting gas, and deposition is or less by using disilane or trisilane as performed at a temperature of 550°C polycrystalline state is obtained. For deposition temperature, and a performed under an amorphous state. CONSTITUTION: Decomposition is example, an amorphous Si film 13 is temperature higher than the Heat treatment is performed at a deposited on an SiO2 film 12 on a Pdeposited. Heat treatment is shape. Thereafter, an SiO2 film 14 is reacting gas at a temperature of 520° method by using Si2H6 gas as a type Si substrate 11 by an LPCVD by heat treatment. BF2 ions are gas, and a gate electrode 15 is deposited by using SiH4 as a reacting implanted in the polycrystalline Si film is obtained. Then, P ions are performed at 900°C, and a gate oxide C. The film is patterned in an island source, a drain and a gate are formed. concentration impurity regions for a implanted, and P-type high formed. Then, an SiO2 film is formed 13. A polycrystalline Si film is

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